RELIABILITY REPORT
FOR

DS2406, Rev A2

Dallas Semiconductor

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Conclusion:

The following qualification successfully meets the quality and reliability standards required of all Dallas Semiconductor products and processes:

DS2406, Rev A2

In addition, Dallas Semiconductor's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at http://www.maxim-ic.com/TechSupport /dsreliability.html.

Device Description:

 A description of this device can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts
AfT = Acceleration factor due to Temperature
 tu = Time at use temperature (e.g. 55°C)
 ts = Time at stress temperature (e.g. 125°C)
  k = Boltzmann's Constant (8.617 x 10-5 eV/°K)
 Tu = Temperature at Use (°K)
 Ts = Temperature at Stress (°K)
 Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

AfV = exp(B*(Vs - Vu))
AfV = Acceleration factor due to Voltage
 Vs = Stress Voltage (e.g. 7.0 volts)
 Vu = Maximum Operating Voltage (e.g. 5.5 volts)
 B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts * AfV * AfT * N * 2)
 X = Chi-Sq statistical upper limit
 N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

FAILURE RATE: **MTTF (YRS): 57112** **FITS: 2.0**

The parameters used to calculate this failure rate are as follows:

Cf: 60% **Ea: 0.7** **B: 0** **Tu: 25 °C** **Vu: 5.5 Volts**

The reliability data follows. A the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data.

Device Information:

Process:	2P, 1M, 0.8um, EPROM, NdDSD, PdDSD/ESD , N+ESDII,
Passivation:	Laser/TEOS Ox - Pass/OxyNit -Gen.LaserP
Die Size:	114 x 77
Number of Transistors:	0
Interconnect:	Aluminum / 1% Silicon / 0.5% Copper
Gate Oxide Thickness:	175 Å

OPERATING LIFE

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QTY	FAILS	FA#
HIGH VOLTAGE LIFE	9607	125C, 6.0 VOLTS	2000	HRS	355	0	
INFANT LIFE	9632	125C, 7.0 VOLTS	48	HRS	380	0	
HIGH VOLTAGE LIFE	9632	125C, 7.0 VOLTS	1000	HRS	116	2	No FA
INFANT LIFE	9711	125C, 6.0 VOLTS	48	HRS	392	0	
HIGH VOLTAGE LIFE	9711	125C, 6.0 VOLTS	2000	HRS	116	0	
INFANT LIFE	9722	125C, 7.0 VOLTS	48	HRS	392	0	
HIGH VOLTAGE LIFE	9722	125C, 7.0 VOLTS	1000	HRS	116	0	
INFANT LIFE	9804	125C, 7.0 VOLTS	48	HRS	345	0	
HIGH VOLTAGE LIFE	9804	125C, 7.0 VOLTS	1000	HRS	150	0	
HIGH VOLTAGE LIFE	9805	125C, 7.0 VOLTS	1000	HRS	116	0	
INFANT LIFE	9821	125C, 7.0 VOLTS	48	HRS	392	0	
HIGH TEMP OP LIFE	9821	125C, 5.5 VOLTS	1000	HRS	116	0	
				Total:		**2**	

STORAGE LIFE

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QTY	FAILS	FA#
STORAGE LIFE	9607	150C	1000	HRS	77	0	
STORAGE LIFE	9632	150C	1000	HRS	77	0	
STORAGE LIFE	9711	150C	1000	HRS	77	0	

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QTY	FAILS	FA#
STORAGE LIFE	9722	150C	1000	HRS	77	0	
STORAGE LIFE	9804	150C	1000	HRS	77	0	
STORAGE LIFE	9805	150C	1000	HRS	77	0	
STORAGE LIFE	9821	150C	1000	HRS	77	0	
				Total:		**0**	

TEMPERATURE CYCLE

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QTY	FAILS	FA#
TEMP CYCLE	9607	-55C TO 125C	1000	CYS	77	0	
TEMP CYCLE	9632	-55C TO 125C	1000	CYS	64	0	
TEMP CYCLE	9711	-55C TO 125C	1000	CYS	77	0	
TEMP CYCLE	9722	-55C TO 125C	1000	CYS	77	0	
TEMP CYCLE	9804	-55C TO 125C	1000	CYS	77	0	
TEMP CYCLE	9821	-55C TO 125C	1000	CYS	77	0	
				Total:		**0**	

TEMPERATURE HUMIDITY BIAS

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QTY	FAILS	FA#
BIASED MOISTURE	9607	85/85, 5.5 VOLTS	959	HRS	77	0	
HAST	9632	120C, 85%R.H.,5.5V	200	HRS	77	0	
BIASED MOISTURE	9711	85/85, 5.5 VOLTS	959	HRS	77	0	
HAST	9722	120C, 85%R.H.,5.5V	100	HRS	77	0	
HAST	9821	120C, 85%R.H.,5.5V	100	HRS	77	0	
				Total:		**0**	

UNBIASED MOISTURE RESISTANCE

DESCRIPTION	DATE CODE	CONDITION	READPOINT		QTY	FAILS	FA#
AUTOCLAVE	9607	121C, 2 ATM STEAM, UNBIASED	168	HRS	44	0	
AUTOCLAVE	9632	121C, 2 ATM STEAM, UNBIASED	168	HRS	45	0	
AUTOCLAVE	9711	121C, 2 ATM STEAM, UNBIASED	168	HRS	45	0	
AUTOCLAVE	9722	121C, 2 ATM STEAM, UNBIASED	168	HRS	43	0	
AUTOCLAVE	9821	121C, 2 ATM STEAM, UNBIASED	168	HRS	45	0	
				Total:		**0**	

FAILURE RATE: **MTTF (YRS): 57112**   **FITS: 2.0**